

Natriumionenkonzentration konstant: magnetohydrodynamik

$C_p = \text{machen}$

$$C_p = \left(\frac{\partial H}{\partial T} \right)_p$$

$$H = H_0 + c_v \Delta H_v$$

↑
hübsch machen angeg.

c_v : valenziale Wärme
(eddig N_v)

$$C_p = C_{p0} + c_v \left(\frac{\partial \Delta H_v}{\partial T} \right)_p + \Delta H_v \left(\frac{\partial c_v}{\partial T} \right)_p$$

$$C_p = C_{p0} + c_v \left\{ \left(\frac{\partial \Delta H_v}{\partial T} \right)_p + \frac{(\Delta H_v)^2}{R T^2} \right\}$$

$$\Delta C_p \approx \frac{c_{v0} (\Delta H_v)^2}{R T^2} \exp \left(- \frac{\Delta H_v}{R T} \right) \approx 0$$

Fig. 10.8. Beispiel AgBr. Leider werden bei höheren T auch anharmonische Effekte sichtbar, s.d. (10.20) nicht zuverlässig ist.

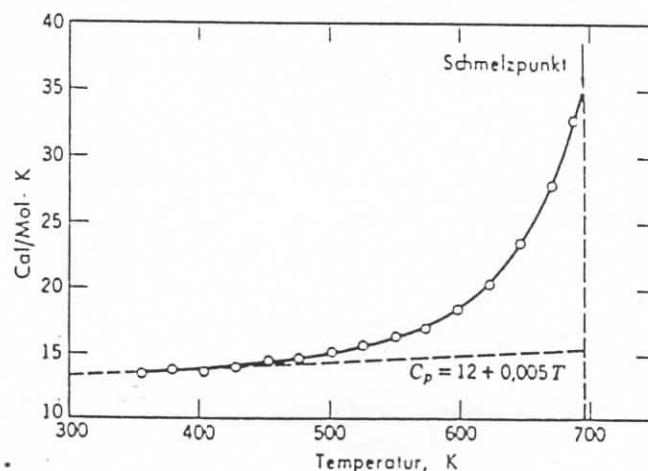


Fig. 10.8.

Molwärme von Silberbromid bei konstantem Druck. Es zeigt sich ein zusätzlicher Beitrag zur spezifischen Wärme, der von der Bildung von Gitterfehlstellen herführt. [Nach R.W. Christy und A.W. Lawson, J. Chem. Phys. 19, 517 (1951).]

2. Phasenübergänge - Diffusionsmechanismus

(Simplifizierte Rollen für V)

Mehrphasen $\nabla = h$ biphasal (T. men.)

$$\frac{\Delta V}{V} \approx 3 \frac{\Delta L}{L}$$

$$\frac{\Delta L}{L} = \frac{1}{3} c_V \frac{V_{tot} - \Omega}{\Omega} + \text{Hysterese}$$

atomistisch

$$\frac{\Delta L}{L} = \frac{\Delta a}{a} = \frac{c_V}{3}$$

$$\frac{\Delta a}{a} = \frac{1}{3} c_V \frac{V_{tot} - \Omega}{\Omega} + \text{Hysterese}$$

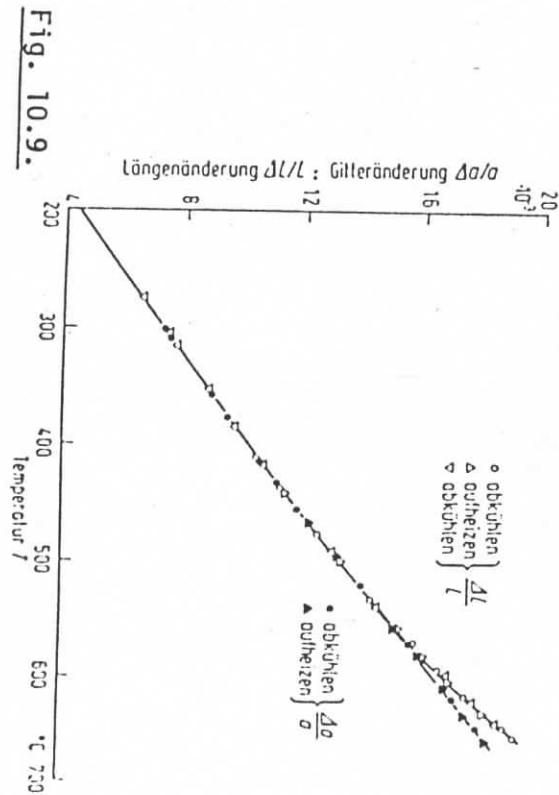


Fig. 10.9.

Punktiert) ergeben im Zinkimminenwirkung (getrocknet) und Gitterparameteränderung (erhöhte Schichtlagentrennen (ausgezogen)). Im Falle der Frenkelpolare ist die Zinkimminenzahl (oder Zahl von J. O. Shimmins und R. W. Balluffi für die Tröpfchen) und Gitterkonstante von Aluminium als Funktion der Temperatur.

Fig. 10.9.: Ergebnisse für Al (siehe auch Fig. 10.7.). Bei hohen Temperaturen ist aber der Einfluss von Doppel leerstellen nicht vernachlässigbar.

3. Technical applications

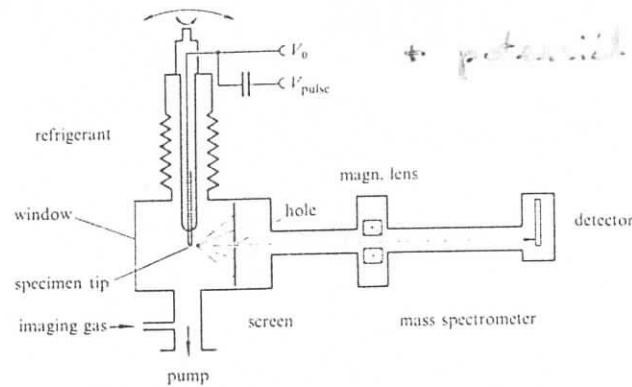


Fig. 2.16. Field ion microscope with moveable tip and mass spectrometer attachment [2.15].

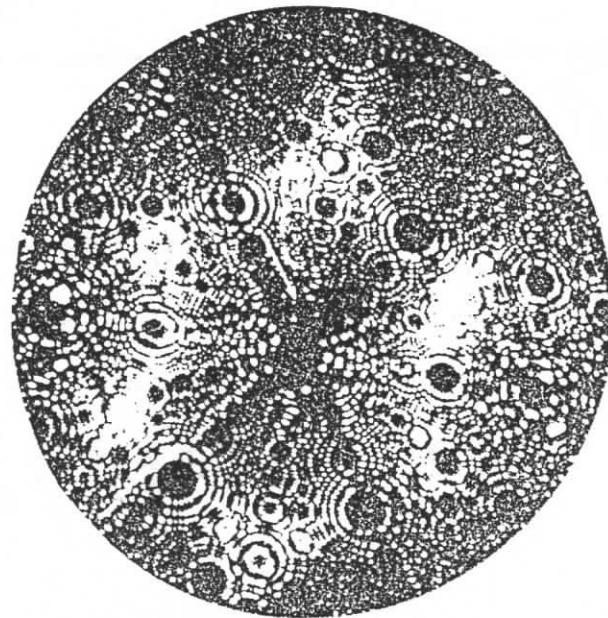


Fig. 2.18. Field ion micrograph of a tungsten tip [2.15].

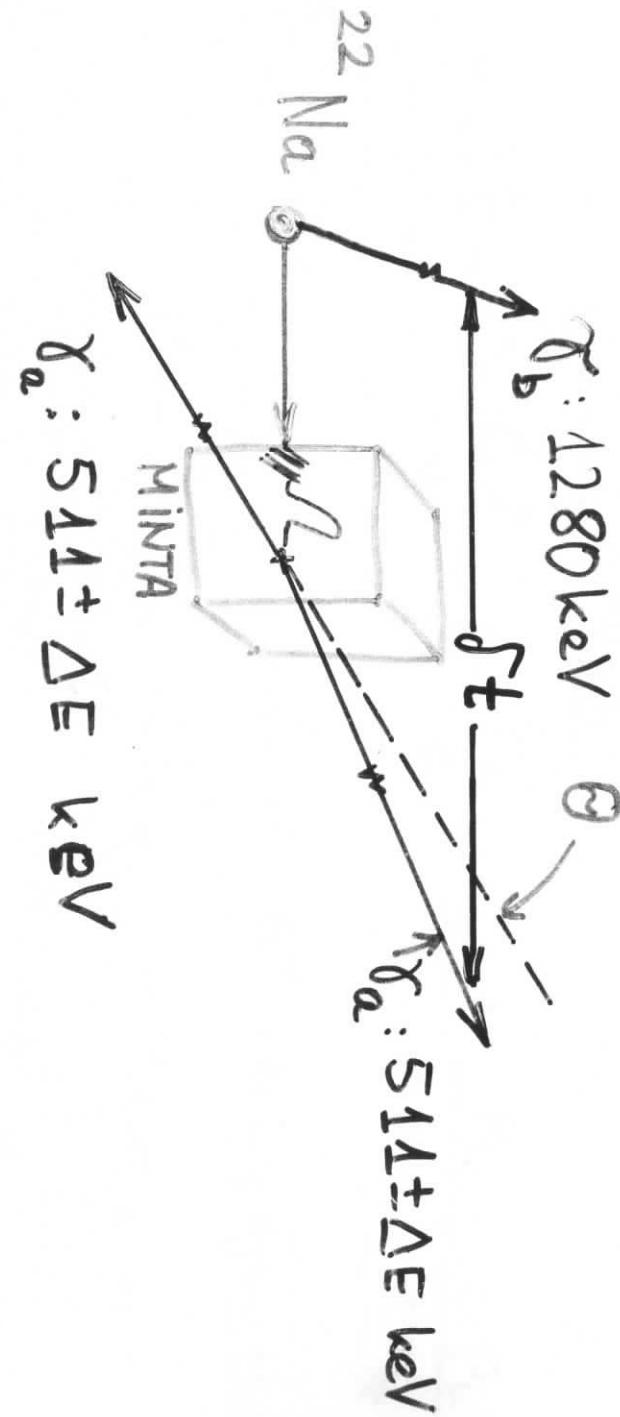
POZITRÓN ANNIHILÁCIÓS

SPEKTROSZKOPIA

(PAS)

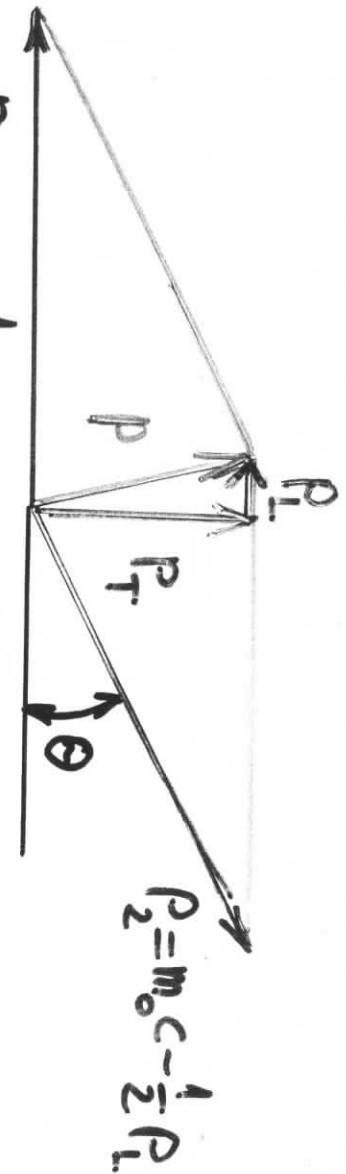


$$\tau_{1/2} = 2.64 \text{ d}$$



PAS módszerek:

- élettartam: δt eloszlás
- Doppler-eltolódás: ΔE
- szög korreláció: Θ



$$P_L = m_0 c + \frac{1}{2} P$$

$$\theta \approx \frac{P_T}{m_0 c}$$

$$\Delta E = E \cdot \frac{\Delta v}{v} = E \cdot \frac{v_L}{c} = m_0 c^2 \cdot \frac{P_L}{2 m_0 c} = \frac{c \cdot P_L}{2 m_0}$$

Élettartam:

bejövő e^+ energiája $\lesssim 100$ GeV

Termálizáció \sim ps

τ : elektronus "lívés" határonna meg.

Fémekben: $\tau_f \sim 100-250$ ps

$\tau_{\text{kiba}} \sim 150-600$ ps

Pt: Al

$$\tau_f = 166 \pm 2 \text{ ps}$$

$$\tau_{4V} = 246 \pm 10 \text{ ps}$$

$$\tau_u = 450 \pm 20 \text{ ps}$$

(2)

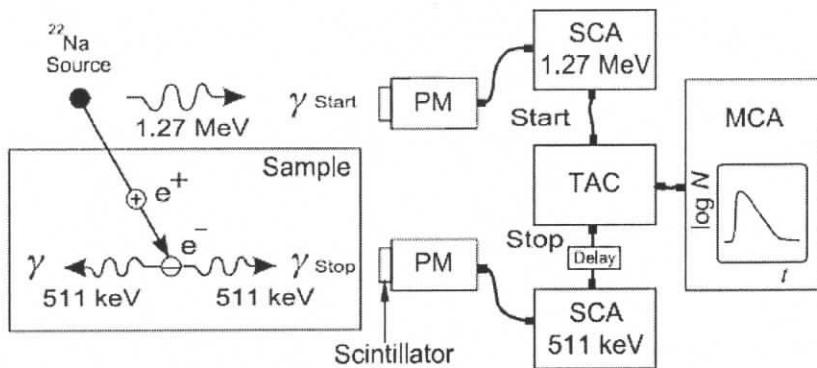


Fig. 1. Scheme of the positron lifetime experiment in fast–fast coincidence. The lifetime is measured as the time difference between the appearance of the start and stop γ -quanta (PM—photomultiplier, SCA—single-channel analyzer). The amplitude of the time-to-amplitude converter (TAC) analog output pulse is proportional to this time difference. The whole lifetime spectrum $N(t)$ is stored in a multi-channel analyzer (MCA).

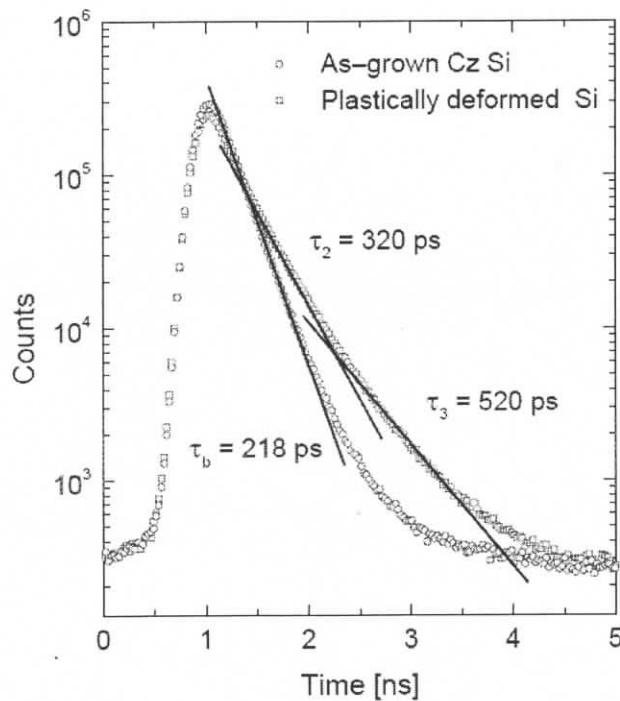


Fig. 2. Experimental positron lifetime spectra obtained in as-grown and in plastically deformed Czochralski-grown (Cz) silicon (Hübner et al. 1997b). The curve of the deformed sample (3 % strain, deformation temperature 775 °C), is located significantly higher, indicating the occurrence of long-lived lifetime components. After the decomposition of the upper spectrum, the obtained lifetime components τ_2 and τ_3 are added as straight lines in the semi-logarithmic plot for illustration. The τ_1 component is not indicated as a straight line ($\tau_1 = 120$ ps). Only one lifetime component corresponding to the positron bulk lifetime τ_b is found in the as-grown sample. The deviations from the straight line at higher times are due to annihilations in the source and the background contribution. The Gaussian-like shape of the left part of the curve is mainly caused by the resolution function.

5.) Befestigungskontaktwiderstände

Hinzu kommen bei der Befestigungskontaktwiderstand des Querdrähtes

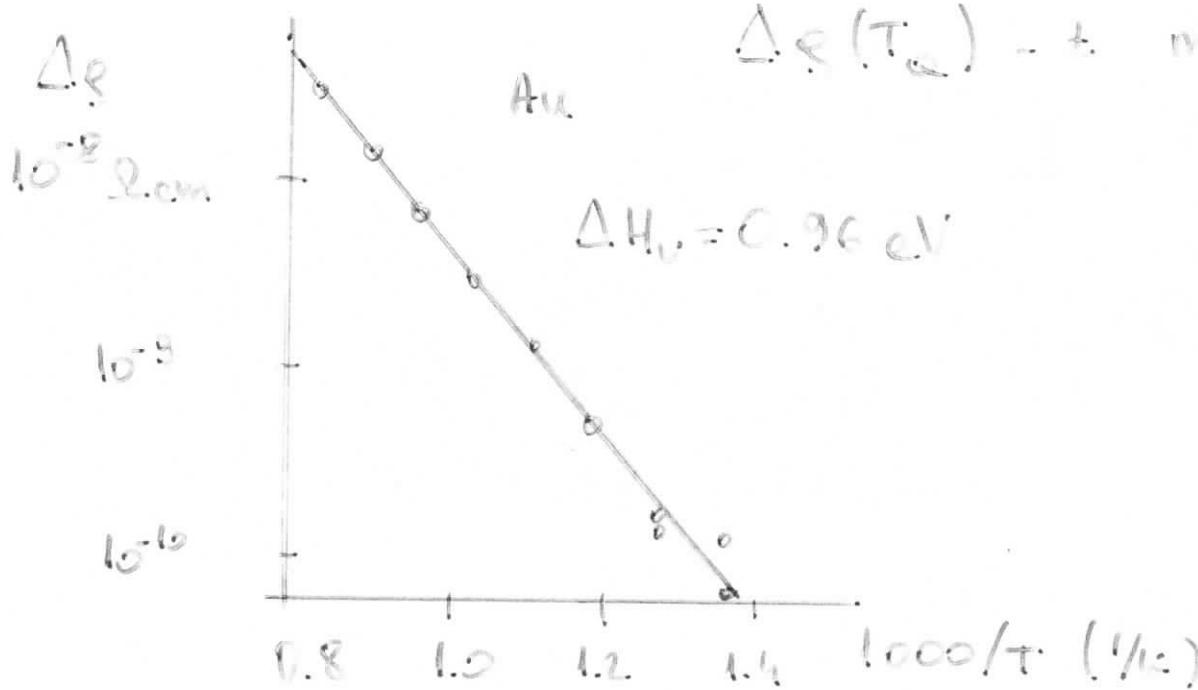
$$T_a \propto \frac{1}{T_A} \quad 10^3 - 10^4 \text{ K/K}$$

$$\Delta(\text{parameter}) \sim c_v$$

pl: ΔS ; ΔV
fikt. dikt. \rightarrow hier fest

Feststellen: T_A -> norm. Widerstand $\propto c_v$

$$\Delta S(T_a) \rightarrow \text{mehr}$$



Kilometer und mindestens mit der
Atominteraktion.

c_v messen \swarrow Massen T in situ - technische
Nahwärme \searrow abkühlung T - befragende
V-sites signal

Nichtionale monovalente ionen!

$$c_v = c_{1v} + 2c_{2v} + \dots = \sum n c_{nv}$$

$n > 2$ Umgeht dann older-
lichem

$$c_v = c_{1v} + 2c_{2v} = \exp\left(\frac{\Delta S^f}{k}\right) \exp\left(-\frac{\Delta H^f}{kT}\right) +$$
$$+ \frac{2}{3} g_{2v} \exp\left[\frac{2\Delta S^f - \Delta S^b}{k}\right] \exp\left(-\frac{2\Delta H^f - \Delta H^b}{kT}\right)$$

geom. temperatur (fcc-hanf)
Dir. Kopplung enthalpie:

$$\Delta H_{2v} = 2\Delta H_v - \Delta H_{1v}^b$$

Wertes: art., da: 2 einschließlich
Wert magnetarumit

PL. Al-na: $\Delta H_v = 0.65 \text{ eV}$ | $\Delta H_{1v}^b = 0.25 \text{ eV}$

$c_v \ll c_v$ da c_v/c_v vs T normaliz.
rel.

Chap. 10.2.5 Kondo et al.

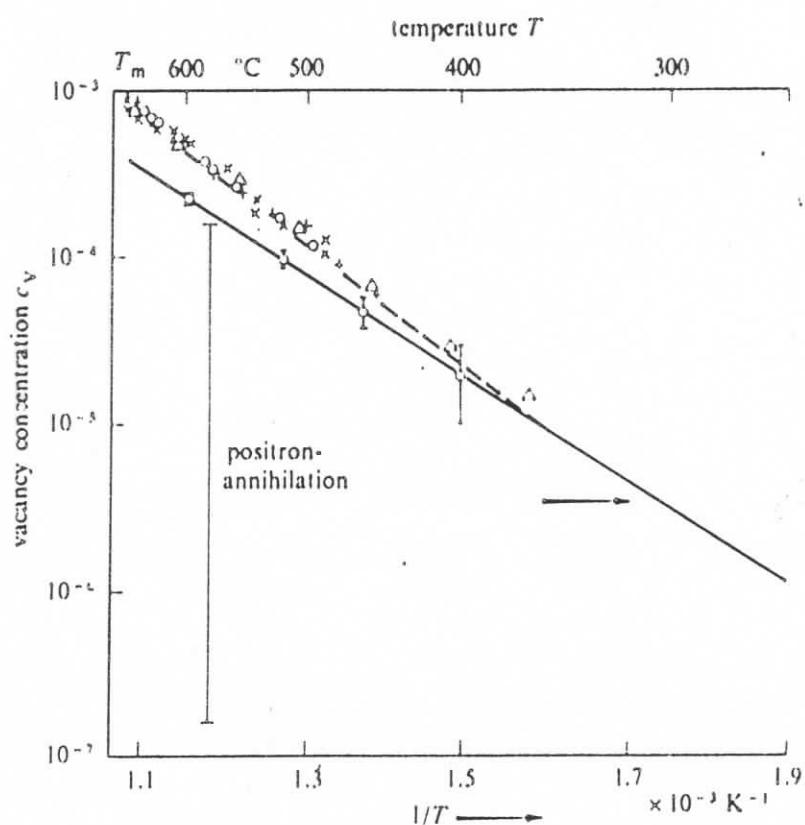


Fig. 10.2. Experimental results of various authors for the T -dependence of $c_v = 3(\Delta l/l - \Delta a/a)$ in aluminium. The experimental errors give rise to an uncertainty $\Delta c_v = \pm 10^{-5}$ shown as four error bars. Measurements of the positron lifetime at vacancies give the slope of the full line in the range shown accurate to $\pm 10^{-7}$. The maximum sensitivity of this method is at $c_v \approx 5 \times 10^{-6}$ (arrow). The open triangles are derived from measurements of the specific heat. After A. Seeger [10.1].

Nincs megállható módszer c_v és c_{vv} mérésére.

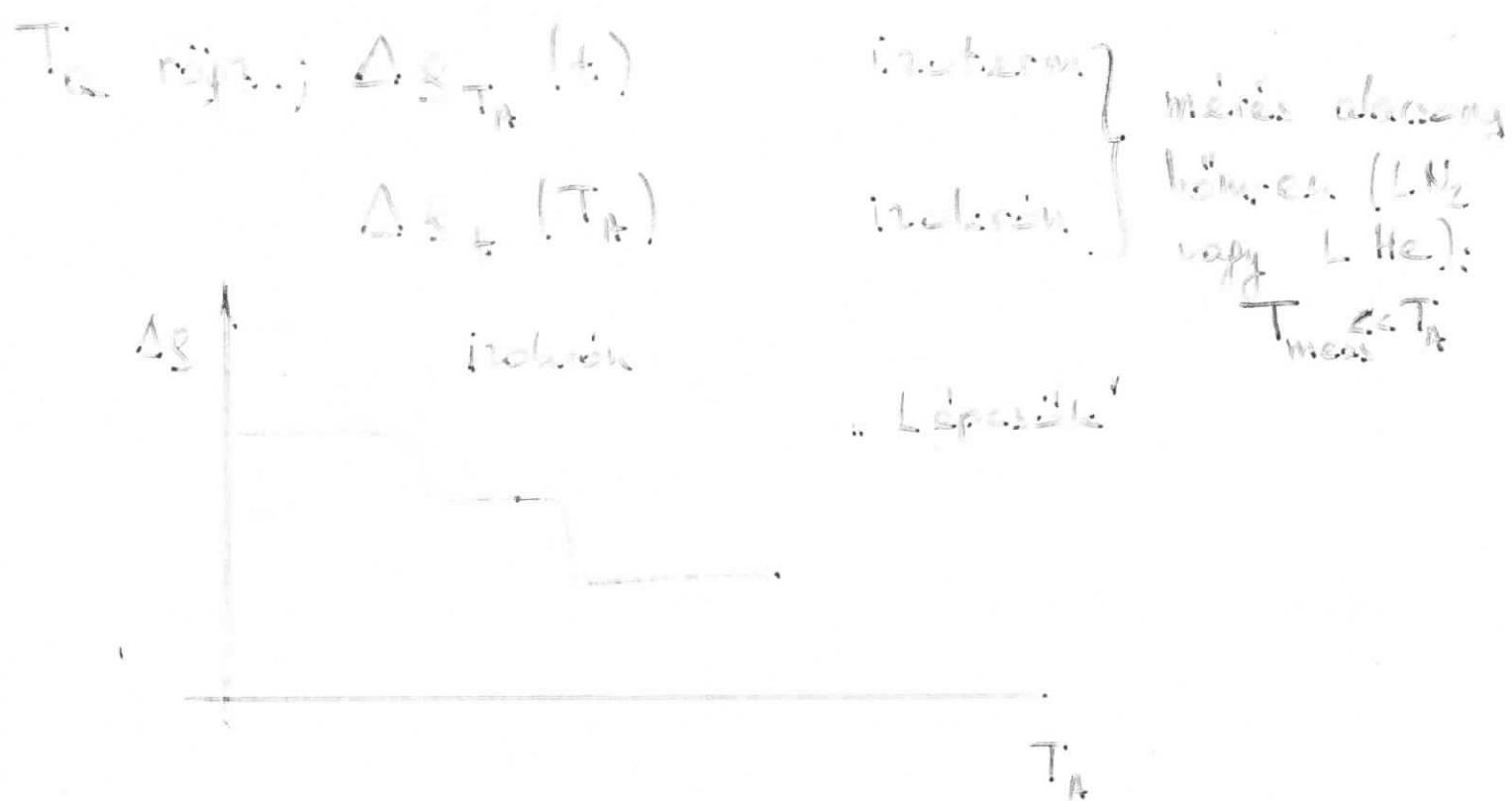
$$\Delta H_v^{\text{eff}} = - \frac{d \ln c_v(T)}{d(1/T)} = \Delta H_v - 2 g_{2v} \quad \Delta H_v - \Delta H_{2v}^b$$

ΔH_v^{eff} T -függő!

bonyolult T -függ.

FIM: felületen tör hozzá néhány lemezként!

Befolyásoló téma + kifejtés



Izoterm kitemperálás

$$c_v(T_A) \ll c_v(T_B)$$

$\Delta S_{T_A}(t)$ csökken amikor $c_v = c_v(T_B)$
be nem áll.

Hogyan működik a V a kristályban?



$$v_V = v_0 \exp\left(-\frac{\Delta G_{VM}}{kT}\right)$$

$$\Delta G_{VM} = \Delta H_{VM} - T \Delta S_{VM}$$

morfológiai

$$v_i = \underbrace{v_0}_{v_0'} e^{\frac{\Delta S_{VM}}{kT}} e^{-\frac{\Delta H_{VM}}{kT}}$$

Kitörésgátlású folyamatok



! döntő:

$$\frac{dc_V}{dt} = 2K_2 c_V - 2K_1 c_V^2 - K_3 c_V \dots a)$$

$$\frac{dc_{2V}}{dt} = K_1 c_V^2 - K_2 c_{2V} - K_3 c_{2V} \dots b)$$

(sok NN körrel) és fcc részöt vizsgálva:

$$K_1 = 42 v_0 \exp\left(-\frac{\Delta H_{VM}}{kT}\right) = 42 v_0$$

$$K_2 = 7 v_0 \exp\left(-\frac{\Delta H_{VM} + \Delta H_{2V}^b}{kT}\right) = 7 v_0 \exp\left(\frac{\Delta H_{2V}^b}{kT}\right)$$

$$K_3 = N a^2 v_0$$

N: dislokációs sűrűség,
nyelők diszl.-k amelyek
 minden belépő V-t elengedik

$$K_3 = N a^2 v_{2V} =$$

$$= N a^2 v_0 \exp\left(-\frac{\Delta H_{2VM}}{kT}\right)$$

7: egy 2V-beli V 12 első szomszédjáról
5 elsőszomszédja a másik V-nak is,
ezekkel hidba kerül helyet.

a) és b) reakcióegy. nem hibridizálható
előford., csatl. spec. szerkez.

Pkt.: c_{2V} nem változik (dim. egyenl.)

$$\frac{dc_{2V}}{dt} = 0 \quad b) \Rightarrow c_{2V} = \frac{K_1 c_W^2}{K_2 + K_1}$$

(ha tövábbi $K_1 < K_2$)

$$\frac{dc_{2V}}{dt} = 0 = K_1 c_W^2 - K_2 c_{2V}$$

$$c_{2V} = \frac{K_1}{K_2} c_W^2 = 6 \exp \frac{\Delta H_{2V}^\circ}{k_B T} c_W^2$$

6 kül. 2V irány fürtben
ezért (ii) fö K_b-ben a'12)

$c_W \rightarrow a)$ és $c_W(t=0) = c_{W0}$ jelöléssel

$$\frac{1}{c_W} = \left[\left(\beta + \frac{1}{c_{W0}} \right) \exp(K_3 t) - \beta \right],$$

ahol $\beta = \frac{2K_1}{K_3} \cdot \left(1 - \frac{K_2}{K_2 + K_1} \right)$

$K_3 t \ll 1$ - re sorfejtéssel:

$$\frac{1}{c_W} - \frac{1}{c_{W0}} = \left(\beta + \frac{1}{c_{W0}} \right) K_3 t$$

$$\Delta \left(\frac{1}{c_W} \right)_n t = - \frac{dc_W}{dt} n \left(-c_W^2 \right)$$

2. rendű folyamat.

$K_3 t \gg 1$:

$$-\frac{dc_N}{dt} \sim c_N$$

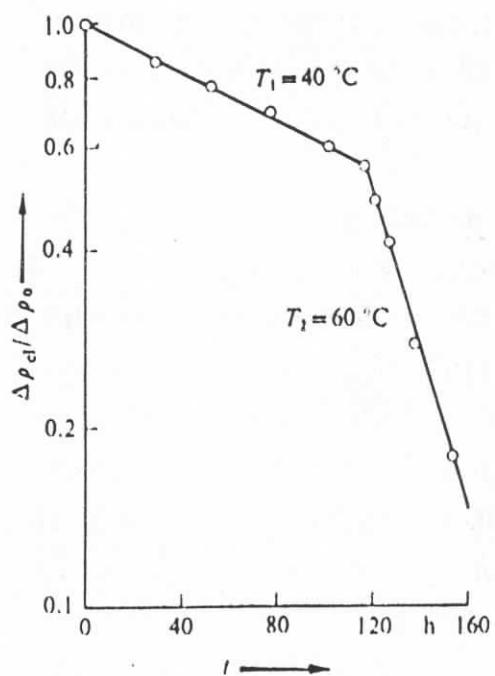
$$\frac{c_N}{c_{N0}} = \frac{1}{1 + \beta c_{N0}} \exp(-K_3 t)$$

Kísérletektől: $-\Delta \left[\ln \left(\frac{c_N}{c_{N0}} \right) \right] / \Delta \left(\frac{1}{T} \right) \rightarrow \Delta H_{Vm}^{\text{eff}}$

$\Delta H_{Vm}^{\text{eff}} \neq \Delta H_{Vm}$; ΔH_{Zm} és ezek nem nagyon eltérőek.

Pt. Au: $\Delta H_{Vm}^{\text{eff}} \approx 0.83 \text{ eV}$

$\Delta H_{Zm} \approx 0.79 \text{ eV}$



$$\ln \left(\frac{\Delta \dot{\rho}(T_2)}{\Delta \dot{\rho}(T_1)} \right) \sim \frac{(-\Delta H_{Vm}/kT_1)}{(-\Delta H_{Vm}/kT_2)}$$

Au: $\Delta H_{Vm} = 0.83 \text{ eV}$

Fig. 10.4. The fraction $\Delta \rho_e / \Delta \rho_0$ of the change in residual resistance remaining in gold wires quenched from $700 \text{ }^\circ\text{C}$ after tempering for t hours at $40 \text{ }^\circ\text{C}$ or $60 \text{ }^\circ\text{C}$.

Quench - körben használjuk a módszert.

Hőtartási szab.: \dot{T}

H. f.: Hug's nézete ki $c_w(T)$ és $c_{2v}(T)$

Au-ban? $\dot{T} = 3 \times 10^4 \text{ K s}^{-1}$; $T_0 = 800^\circ\text{C}$

$$N = 5 \times 10^{27} / \text{cm}^3$$

$$\Delta H_{WV} = 0.89 \text{ eV}$$

$$\Delta H_{2VW} = 0.71 \text{ eV}$$

$$\underline{\Delta H_{2V}^b = 0.35 \text{ eV}}$$

További problémák: - V-es operátorok is képződnek
- idegen atomok

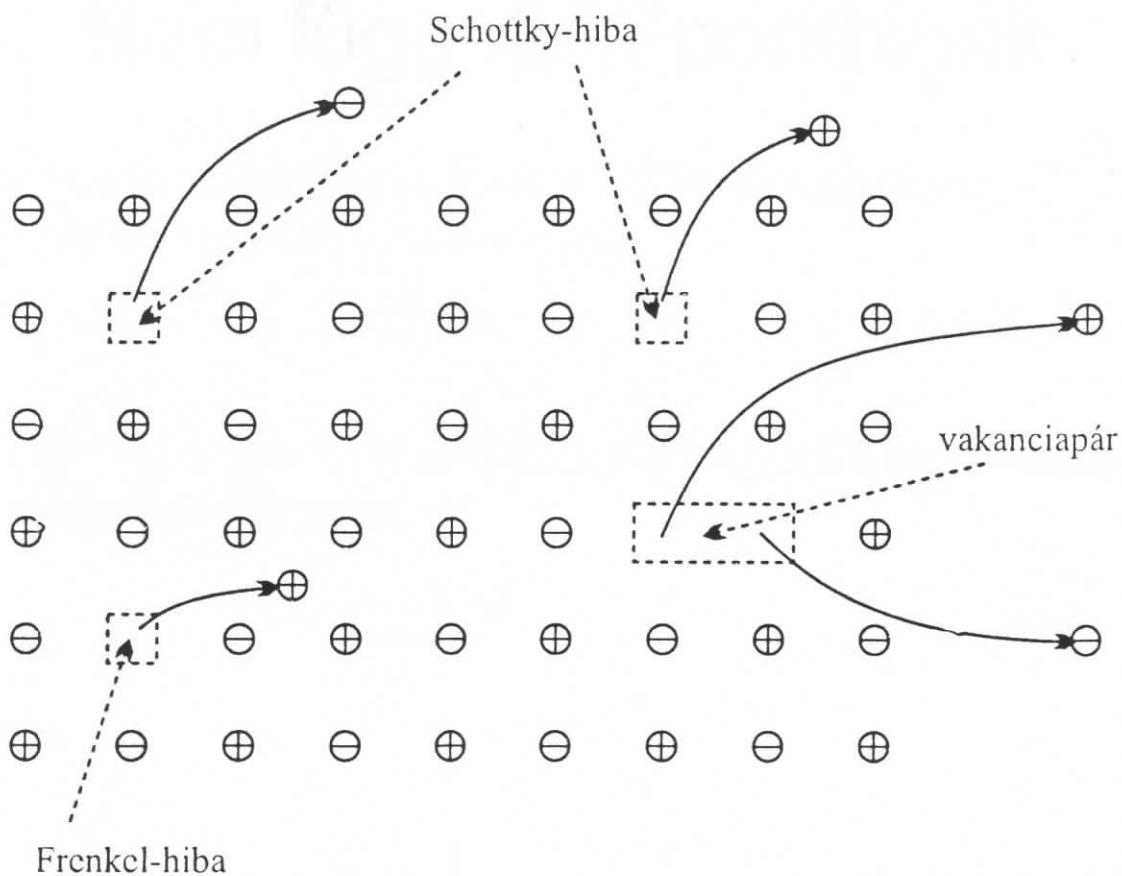
V-esoperátorok FIM-mel TEM-mel megfigyelhetők

sikbeli (\rightarrow dislokációhurok) \rightarrow
 \rightarrow 3D (prizmatikus)

Idegen atomok: atomteret és elterő töltést gyakran vannak teh. V-val $\approx 0.1 \text{ eV}$

Hatás diffúzióra, kiválási folyamatokra

Kristályhibák ionos rácsban



Szennyező ionnal keltett vakancia

Nem független ponthibák

Ionos kristályoknál a lokális töltéssemlegesség megkövetelése is szükséges.

$$\sum_j q_j n_j = 0$$

Ezt Lagrange-multiplikátorokkal vehetjük figyelembe a szabadenergiában.

$$G + \lambda \sum_j q_j n_j$$

$$n_j = N_j e^{-\frac{\varepsilon_j + \lambda q_j}{k_B T}}$$

Legegyszerűbb eset:

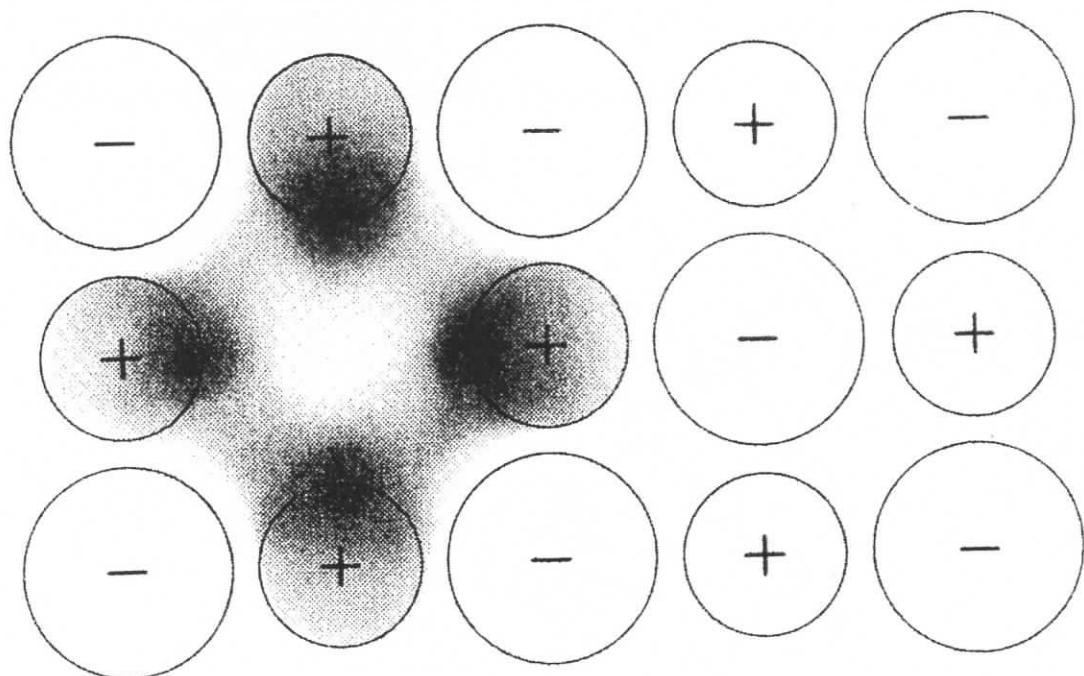
q és $-q$ töltésű ionokból álló rács. Vakanciák keltési energiája ε_- és ε_+ , számuk n_- és n_+ .

$$n_+ = N e^{-\frac{\varepsilon_+ + \lambda q}{k_B T}} \quad n_- = N e^{-\frac{\varepsilon_- - \lambda q}{k_B T}}$$

Töltéssemlegesség feltétele: $n_+ = n_- \quad \lambda q = \frac{\varepsilon_- - \varepsilon_+}{2}$

$$n_+ = n_- = N e^{-\frac{\varepsilon_+ + \varepsilon_-}{2 k_B T}}$$

Színcentrumok

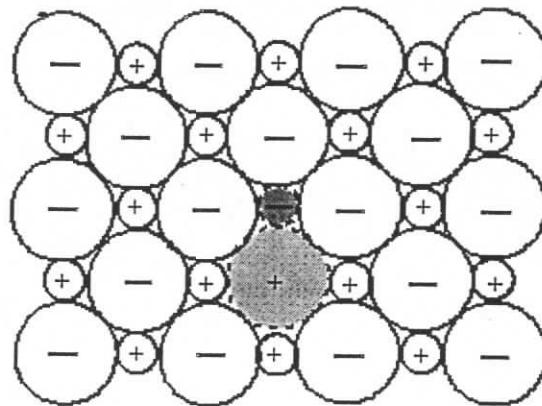


F-centrum

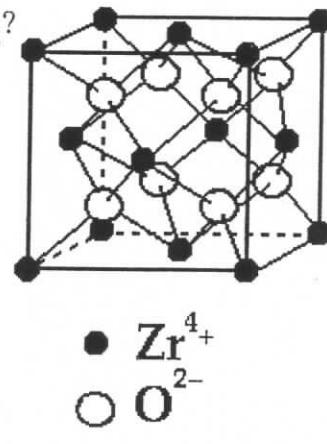
Point Defects in Ionic Solids

- Vacancies are required in ionic solids, just like they are for other types, BUT
- The vacancies must be formed in such a way that the solid remains **charge neutral**.
- Single vacancies cannot be formed because they leave behind a **charge center**.
- Two main ways to create point defects in ionic solids without causing charge imbalance:
 - Correlated vacancies: **Schottky** defects
 - Correlated vacancy-interstitial groups: **Frenkel** defects

Schottky Defects: [100] NaCl

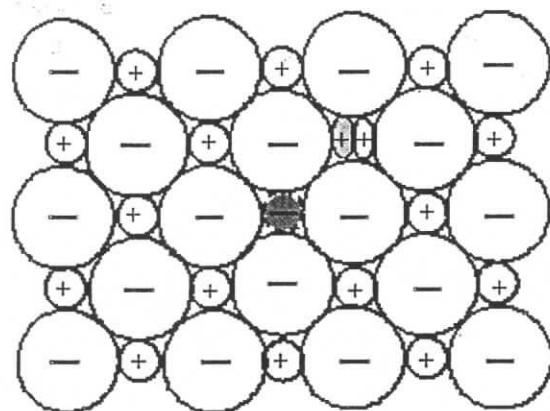


Exercise: What is the most likely Schottky defect structure in ZrO_2 ?



Point Defects in Ionic Solids

Frenkel Defects: [100] MgO



Exercise: What is the most likely Frenkel defect in ZrO_2 ?